

SOT-23 Plastic-Encapsulate Transistors

MMBT4401

TRANSISTOR (NPN)

FEATURES

Switching transistor

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	600	mA
P_C	Collector Power dissipation	0.3	W
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55to +150	$^{\circ}\text{C}$
$R_{\theta JA}$	Thermal Resistance, junction to Ambient	357	$^{\circ}\text{C}/\text{mW}$

SOT-23



1. BASE
2. EMITTER
3. COLLECTOR

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}$, $I_E = 0$	60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}$, $I_B = 0$	40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100\mu\text{A}$, $I_C = 0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB} = 50\text{V}$, $I_E = 0$		0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = 30\text{V}$, $I_B = 0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5\text{V}$, $I_C = 0$		0.1	μA
DC current gain	h_{FE}	$V_{CE} = 1\text{V}$, $I_C = 150\text{mA}$	100	300	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 150\text{mA}$, $I_B = 15\text{mA}$		0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 150\text{mA}$, $I_B = 15\text{mA}$		0.95	V
Transition frequency	f_T	$V_{CE} = 10\text{V}$, $I_C = 20\text{mA}$ $f = 100\text{MHz}$	250		MHz

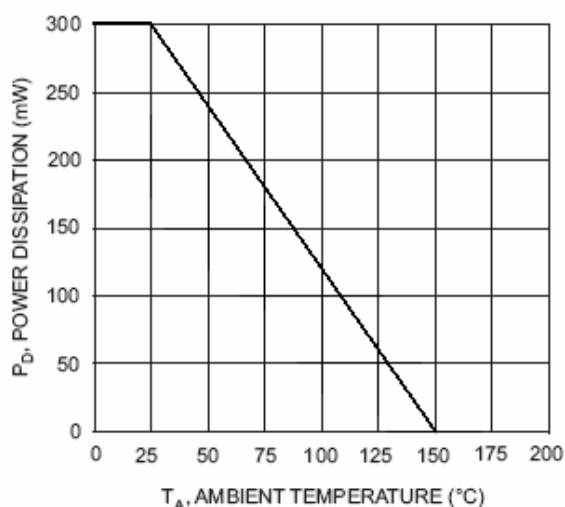


Fig. 1 Max Power Dissipation vs Ambient Temperature

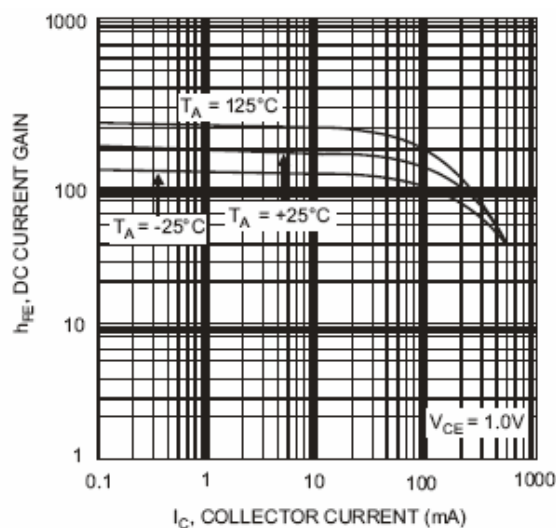


Fig. 2 Typical DC Current Gain vs Collector Current

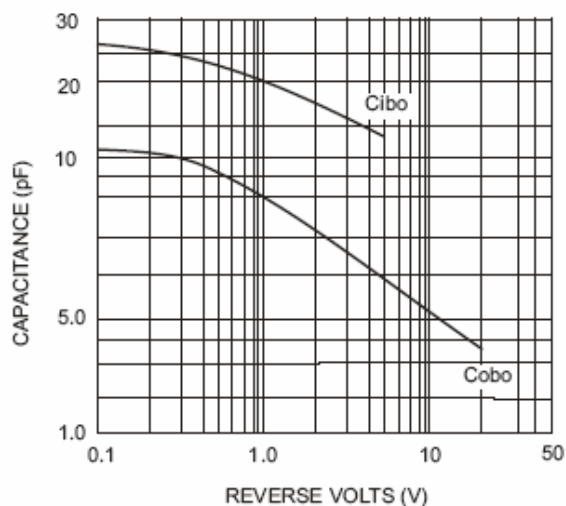


Fig. 3 Typical Capacitance

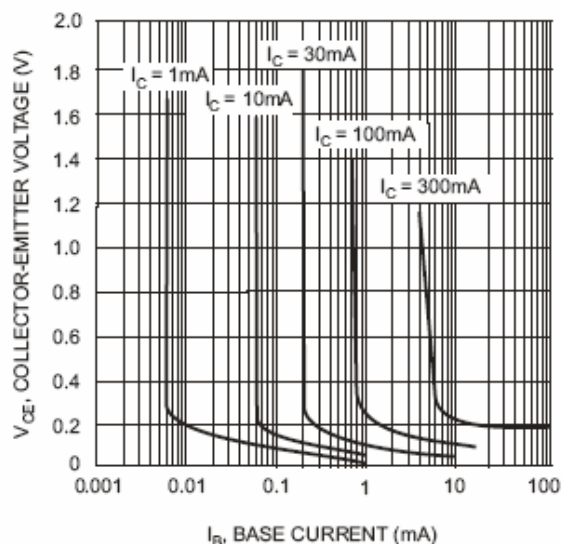


Fig. 4 Typical Collector Saturation Region

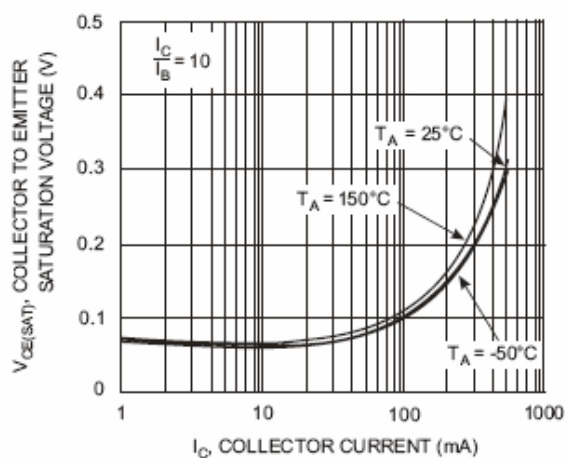


Fig. 5 Collector Emitter Saturation Voltage vs. Collector Current

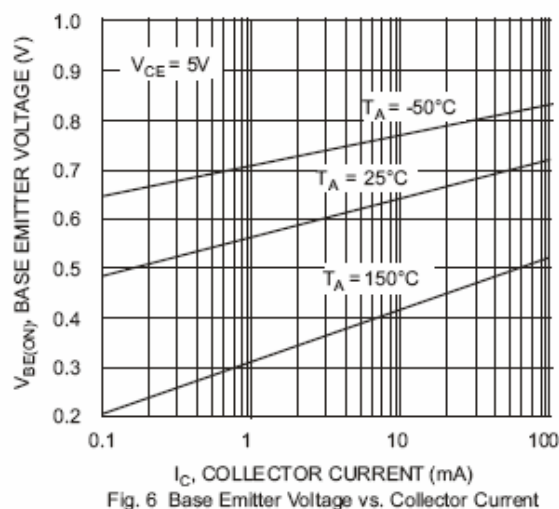


Fig. 6 Base Emitter Voltage vs. Collector Current